NSN 5961-01-272-8945

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View Online at https://aerobasegroup.com/nsn/5961-01-272-8945
Inclosure Material:
Metal
Overall Length:
Between 0.890 inches and 0.910 inches
Overall Height:
Between 0.140 inches and 0.200 inches
Overall Width:
Between 0.375 inches and 0.395 inches
Mounting Facility Quantity:
2
Internal Configuration:
Junction contact
Electrode Internally-electrically Connected To Case:
Emitter
Mounting Method:
Unthreaded hole
Features Provided:
High frequency and gold plated leads
Semiconductor Material:
Silicon
Voltage Rating In Volts Per Characteristic:
30.0 breakdown voltage, collector-to-emitter, base open and 65.0 breakdown voltage, collector-to-base, emitter open and 4.0 breakdown
voltage, emitter-to-base, collector open
Current Rating Per Characteristic:
3.00 amperes source cutoff current
Power Rating Per Characteristic:
44.0 watts small-signal input power, common-collector absolute
Maximum Operating Tempurature Per Measurement Point:
200.0 degrees celsius junction
Special Features:
Junction pattern arrangement: npn
Precious Material And Location:
Plated leads. Gold
Precious Material:
Gold
Test Data Document:
53711-5538013 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.;
excludes any specification, standard or other document that may be referenced in a basic governing drawing)
Terminal Type And Quantity:
3 ribbon and 1 case
Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

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